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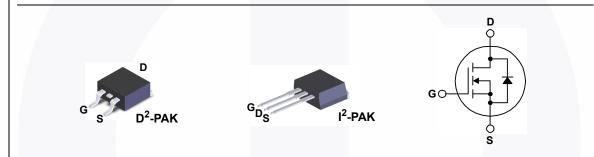
FQB50N06 / FQI50N06 N-Channel QFET[®] MOSFET 60 V, 50 A, 22 mΩ

Description

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, audio amplifier, DC motor control, and variable switching power applications.

Features

- + 50 A , 60 V, $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}$ = 22 m Ω (Max.) @V_{GS} = 10 V, I_D = 25 A
- Low Gate Charge (Typ. 31 nC)
- Low Crss Typ. 65 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating



Absolute Maximum Ratings T_c = 25°C unless otherwise noted

Symbol	Parameter		FQB50N06TM / FQI50N06TU	Unit
V _{DSS}	Drain-Source Voltage		60	V
I _D	Drain Current - Continuous ($T_C = 25^\circ$	°C)	50	А
	- Continuous (T _C = 100	D°C)	35.4	А
I _{DM}	Drain Current - Pulsed	(Note 1)	200	А
V _{GSS}	Gate-Source Voltage		± 25	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	490	mJ
I _{AR}	Avalanche Current	(Note 1)	50	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	12	mJ
dv/dt	Peak Diode Recovery dv/dt (N		7.0	V/ns
P _D	Power Dissipation $(T_A = 25^{\circ}C)^{*}$		3.75	W
	Power Dissipation $(T_C = 25^{\circ}C)$		120	W
	- Derate above 25°C		0.8	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C
TL	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

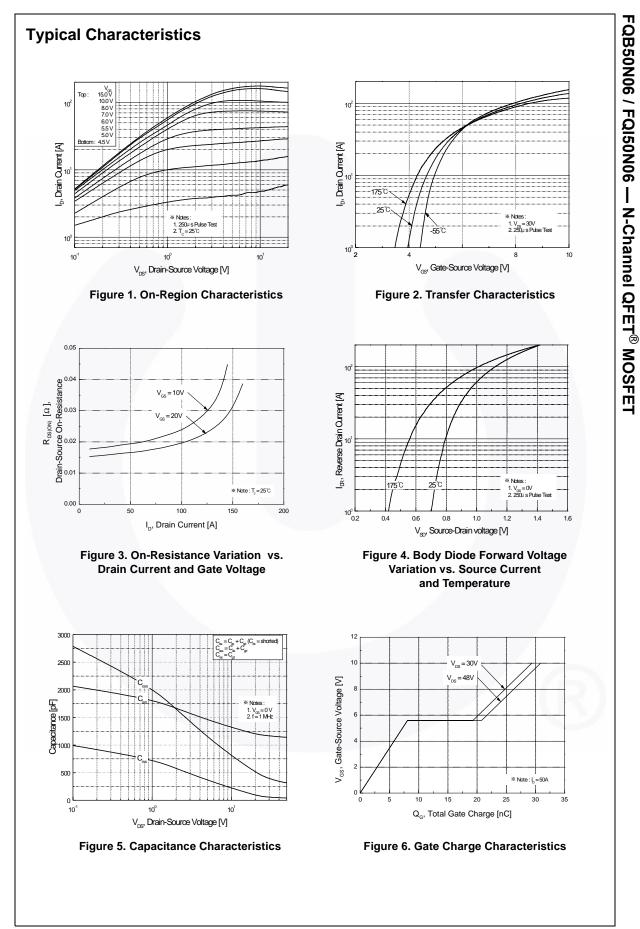
Thermal Characteristics

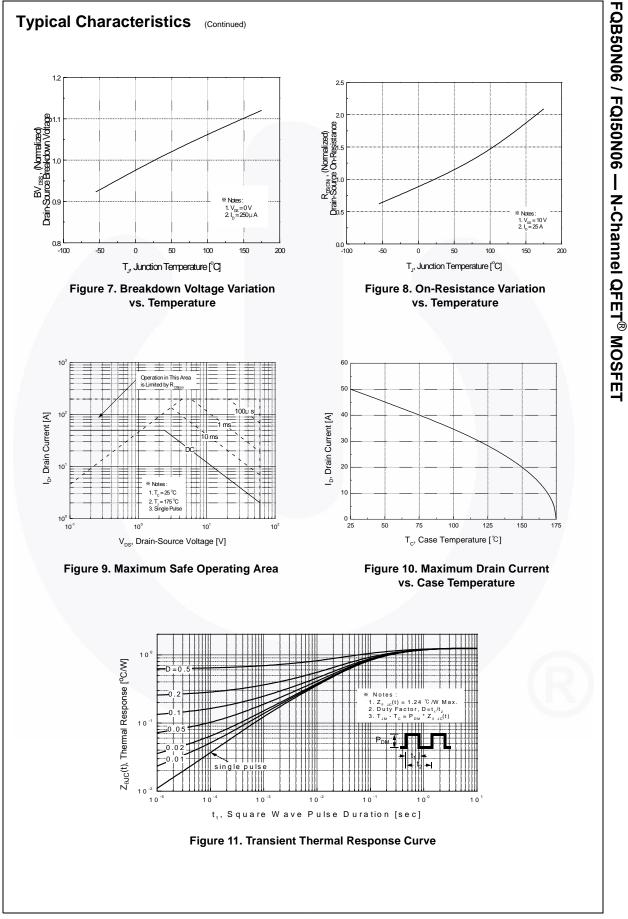
Symbol	Parameter	FQB50N06TM FQI50N06TU	Unit
$R_{ ext{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	1.24	
В	Thermal Resistance, Junction to Ambient (minimum pad of 2 oz copper), Max.	62.5	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient (* 1 in ² pad of 2 oz copper), Max.	40	

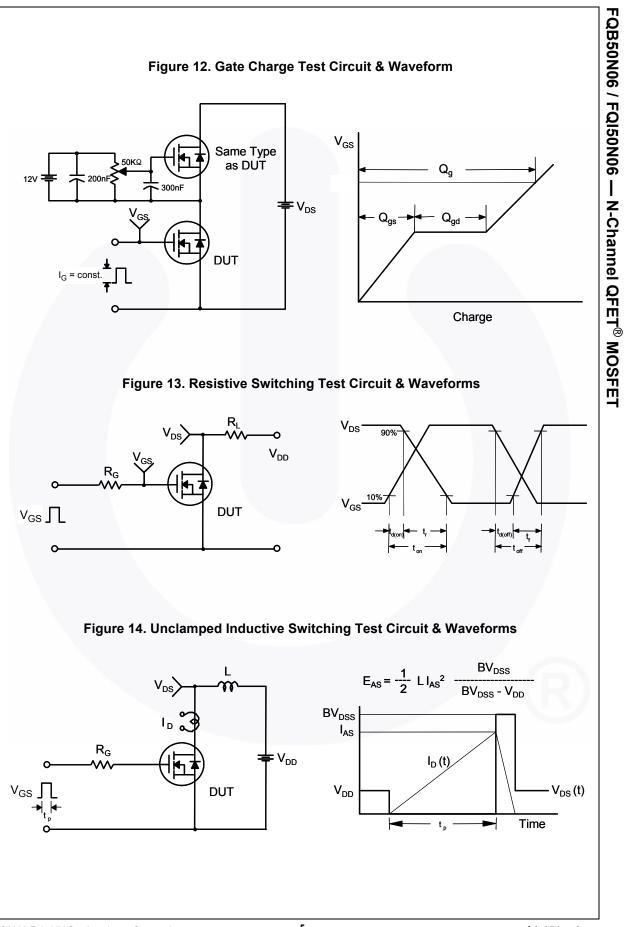
October 2013

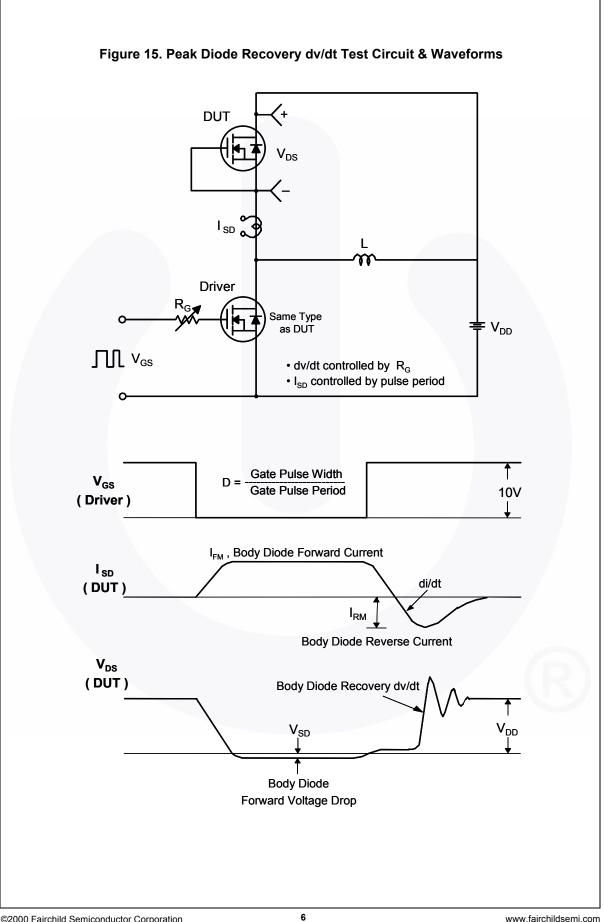
FORMAL	Device Marking Devi		, in the second s		Tape Width		Quantity		
FQB50N06 FQI50N06		FQB50N06TM	D2-PAK	D2-PAK 330mm I2-PAK -		24mm -		800 50	
		FQI50N06TU	I2-PAK						
lectrica	al Ch	aracteristics T _c	= 25°C unless othe	rwise noted					
Symbol		Parameter		Test Conditions		Min	Тур	Max	Unit
Off Chara	actori	stice							
		ource Breakdown Voltage	$V_{CS} = 0$	V, I _D = 250 μA		60			V
		own Voltage Temperature				00			
	Coefficie		$I_{\rm D} = 250$	μA, Referenced to	25°C		0.06		V/°C
220	7		V _{DS} = 6	0 V, V _{GS} = 0 V				1	μA
2	zero Ga	te Voltage Drain Current	$V_{DS} = 4$	8 V, T _C = 150°C				10	μA
GSSF (Gate-Bo	ody Leakage Current, Forw		5 V, V _{DS} = 0 V				100	nA
GSSR (Gate-Bo	ody Leakage Current, Reve	erse V _{GS} = -	25 V, V _{DS} = 0 V				-100	nA
On Chara / _{GS(th)} (reshold Voltage		′ _{GS} , I _D = 250 μA		2.0		4.0	V
	Jale II	reshold voltage	v DS − v	GS , $D = 250 \mu A$		2.0		4.0	v
	Statia D	roin Couroo							
R _{DS(on)} S	Static D On-Res	rain-Source stance	V _{GS} =1) V, I _D =25 A			0.018	0.022	Ω
R _{DS(on)} S	On-Res		00	$V, I_{D} = 25 A$ 5 V, I _D = 25 A			0.018 22	0.022	Ω S
R _{DS(on)} (C VFS F Dynamic C _{iss} I	On-Res Forward Char	stance	V _{DS} = 2	5 V, I _D = 25 A					
R _{DS(on)} S (C HFS F Dynamic C _{iss} II	On-Res Forwarc Char	stance Transconductance acteristics	V _{DS} = 2	5 V, I _D = 25 A 5 V, V _{GS} = 0 V,			22		S
R _{DS(on)} S _{DS(on)} S _C S _S Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Coss Co	On-Res Forwarc Char Input Ca Output (istance Transconductance acteristics apacitance	V _{DS} = 2	5 V, I _D = 25 A 5 V, V _{GS} = 0 V,			22 1180	 1540	S pF
RDS(on) S FS F Oynamic Ciss II Coss C Crss F	On-Res Forward Char Input Ca Dutput (Reverse	International State Stat	V _{DS} = 2	5 V, I _D = 25 A 5 V, V _{GS} = 0 V,			22 1180 440	 1540 580	S pF pF
R _{DS(on)} C GFS F Dynamic Ciss II Coss C Crss F Switching	On-Res Forward Char Input Ca Dutput C Reverse g Cha	I Transconductance acteristics apacitance Capacitance	V _{DS} = 2	5 V, I _D = 25 A 5 V, V _{GS} = 0 V, //Hz			22 1180 440	 1540 580	S pF pF
RDS(on) R IFS F Oynamic Ciss In Coss C Crss F Switching d(on) 1	On-Res Forward Char nput Ca Dutput (Reverse g Cha Turn-Or	stance Transconductance acteristics apacitance Capacitance Transfer Capacitance racteristics	V _{DS} = 2 V _{DS} = 2 f = 1.0 M	5 V, $I_D = 25 \text{ A}$ 5 V, $V_{GS} = 0 \text{ V}$, //Hz 0 V, $I_D = 25 \text{ A}$,			22 1180 440 65	 1540 580 90	S pF pF pF
RDS(on) S IFS F Oynamic Ciss I Coss C Crss F Switching I 1 I 1	On-Res Forward Char nput Ca Output (Reverse g Cha Turn-Or Turn-Or	Istance Transconductance acteristics apacitance Capacitance Transfer Capacitance racteristics Delay Time	V _{DS} = 2	5 V, $I_D = 25 \text{ A}$ 5 V, $V_{GS} = 0 \text{ V}$, //Hz 0 V, $I_D = 25 \text{ A}$,			22 1180 440 65 15	 1540 580 90 40	S pF pF pF ns
RDS(on) S IFS F Dynamic Ciss II Coss C Crss F Switching d(on) 1 r 1 d(off) 1	On-Res Forwarc Char nput Ca Dutput C Reverse g Cha Turn-Or Turn-Or	Istance Transconductance acteristics apacitance Capacitance Transfer Capacitance racteristics Delay Time Rise Time	V _{DS} = 2 V _{DS} = 2 f = 1.0 M	5 V, $I_D = 25 \text{ A}$ 5 V, $V_{GS} = 0 \text{ V}$, <i>I</i> Hz 0 V, $I_D = 25 \text{ A}$, Ω	Note 4)		22 1180 440 65 15 105	 1540 580 90 40 220	S pF pF pF ns ns
RDS(on) S IFS F Dynamic Diss II Doss C Crss F Switching d(on) 1 r 1 d(off) 1 f 1	On-Res Forward Dutput Ca Dutput C Reverse g Cha Turn-Or Turn-Of Turn-Of	Instance	V _{DS} = 2 V _{DS} = 2 f = 1.0 M V _{DD} = 3 R _G = 25	5 V, $I_{D} = 25 \text{ A}$ 5 V, $V_{GS} = 0 \text{ V}$, MHz 0 V, $I_{D} = 25 \text{ A}$, $\Omega \Omega$ (1)	Note 4)		22 1180 440 65 15 105 60	 1540 580 90 40 220 130	S pF pF pF ns ns ns
$\begin{array}{c} R_{DS(on)} \\ R_{DS(on)} \\ R_{S} \\ R_{S}$	On-Res Forward Dutput Ca Dutput C Reverse g Cha Turn-Or Turn-Of Turn-Of Turn-Of Total Ga	stance Transconductance acteristics apacitance Capacitance a Transfer Capacitance racteristics Delay Time Rise Time Delay Time Fall Time	V _{DS} = 2 V _{DS} = 2 f = 1.0 M V _{DD} = 3 R _G = 25	5 V, $I_D = 25 \text{ A}$ 5 V, $V_{GS} = 0 \text{ V}$, MHz 0 V, $I_D = 25 \text{ A}$, Ω (1) 8 V, $I_D = 50 \text{ A}$,	Note 4)		22 1180 440 65 15 105 60 65	 1540 580 90 40 220 130 140	S pF pF pF ns ns ns ns

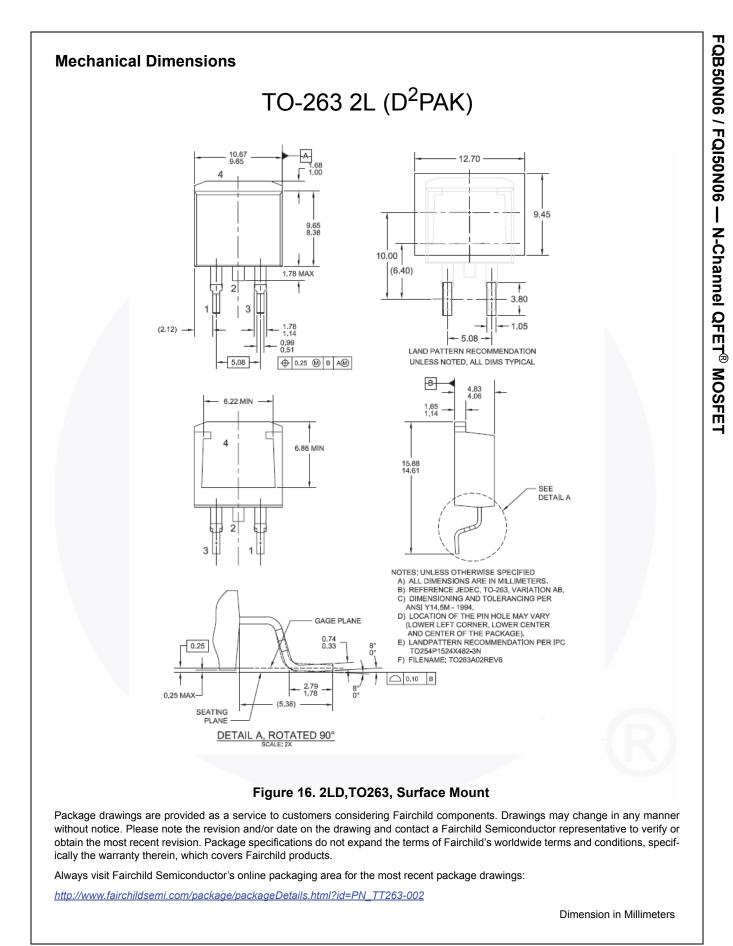
2. L = 230µH, I_{AS} = 50A, V_{DD} = 25V, R_G = 25 Ω, Starting T_J = 25°C 3. I_{SD} \leq 50A, di/dt \leq 300A/µs, V_{DD} \leq BV_{DSS}, Starting T_J = 25°C 4. Essentially independent of operating temperature

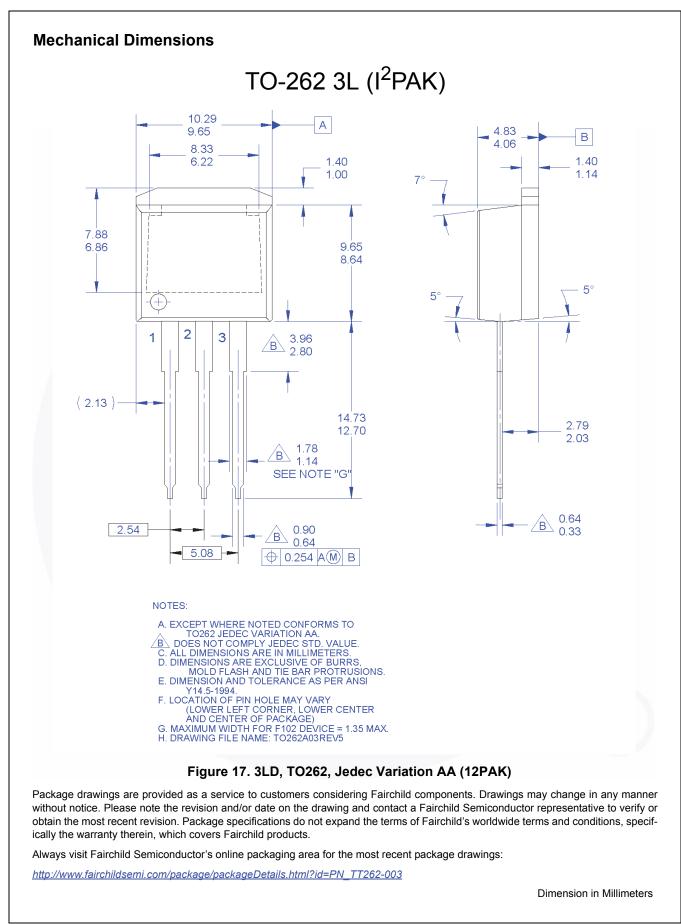














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